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(57) Abstract :

The present disclosure provides a pseudo-resistive element 100, which can provide a highly linear characteristic over a wide range of voltage. The pseudo-resistive element 100 include one or more Metal Oxide Semiconductor transistors configured and coupled to each other in a pre-determined way. A biasing voltage is applied to facilitate operation of the pseudo-resistive element 100. The pseudo-resistive element 100 is capable of providing enhanced performance against Process Voltage and Temperature (PVT) variations.

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